

***Amendment and Response*****Serial No.: 10/003,224****Confirmation No.: 5031****Filed: October 26, 2001****For: SYSTEM AND METHOD FOR CHARACTERIZATION OF THIN FILMS*****Page 2 of 8*****In the Claims**

Please amend claims 10, 12-14 and 23. The amended claims are provided below in clean form. Per 37 C.F.R. §1.121, the amended claims are also shown in Appendix A with notations to indicate changes made (for convenience, all pending claims are provided in Appendix A).

10. (Once Amended) The method of claim 9, wherein using the ion beam comprises providing the ion beam at an ion angle less than or equal to about 20 degrees relative to the sample surface.

12. (Once Amended) The method of claim 1, wherein each of the plurality of samples comprises a thin film having a thickness of less than about 10 nanometers.

13. (Once Amended) The method of claim 4, wherein each of the plurality of samples comprises a thin film having a thickness of less than about 2 nanometers.

14. (Once Amended) The method of claim 13, wherein each of the plurality of samples comprises a gate dielectric film.

23. (Once Amended) The method of claim 22, wherein the thin film of each of the plurality of samples comprises a thickness of less than about 10 nanometers.